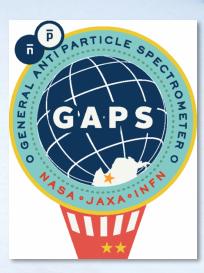
Large-area Si(Li) Detectors for the GAPS Antarctic Balloon Program

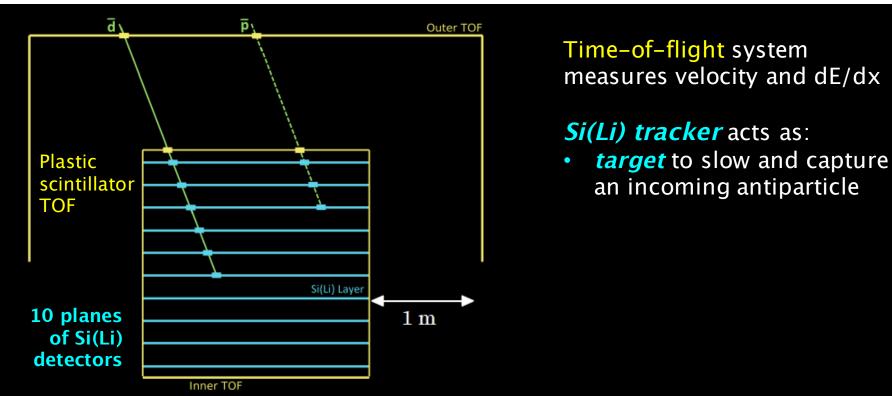
Kerstin Perez

on behalf of the GAPS Si(Li) team

CPAD Instrumentation Frontier Workshop





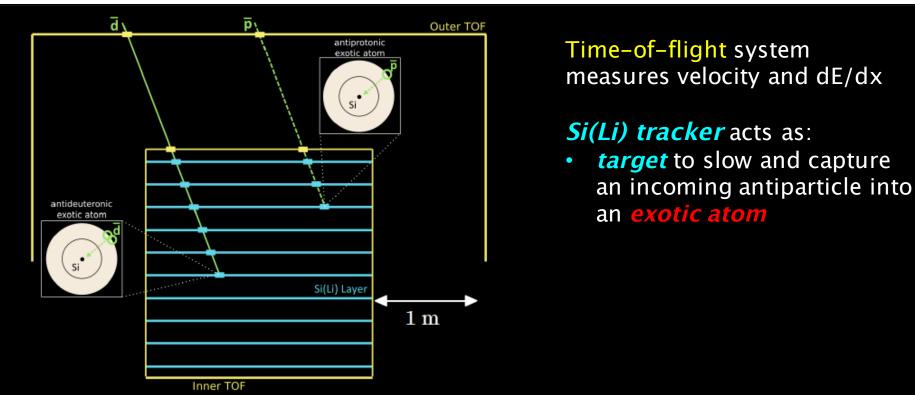


Extoic atom technique verified at KEK: Aramaki+ Astropart.Phys. 49, 52-62 (2013) GAPS sensitivity to antideuterons: Aramaki+ Astropart.Phys. 74, 6 (2016) GAPS sensitivity to antiprotons: Aramaki+ Astropart.Phys. 59, 12-17 (2014)

Illustration credit: A. Lowell (UCSD)

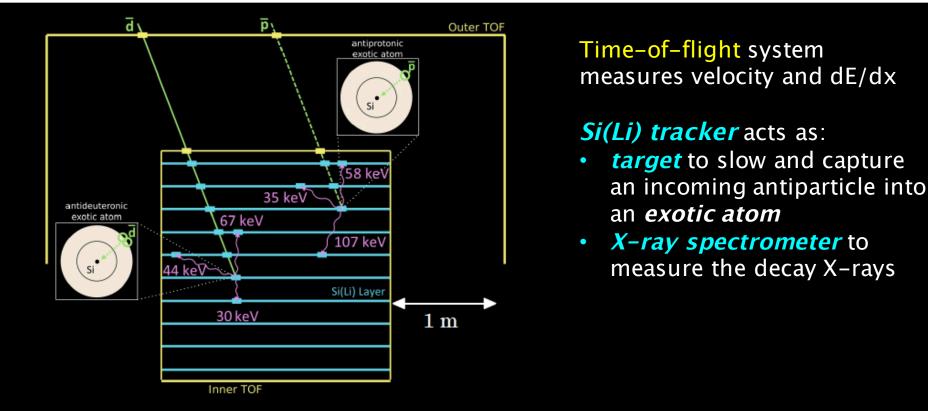
K. Perez – MIT



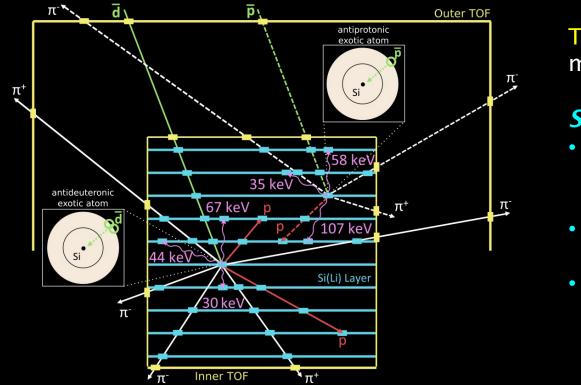


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Time-of-flight system measures velocity and dE/dx

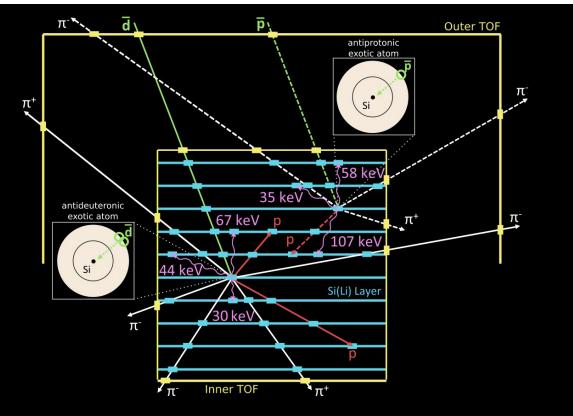
Si(Li) tracker acts as:

- target to slow and capture an incoming antiparticle into an exotic atom
- X-ray spectrometer to measure the decay X-rays
- particle tracker to measure the resulting dE/dX, stopping depth, and annihilation products

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Illustration credit: A. Lowell (UCSD)





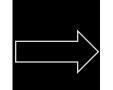
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A rare event search for **antideuterons**: a **dark matter** signature with *essentially zero* conventional astrophysical background

Review of antideuteron experiment and theory: **Phys. Rept. 618 (2016) 1-37**

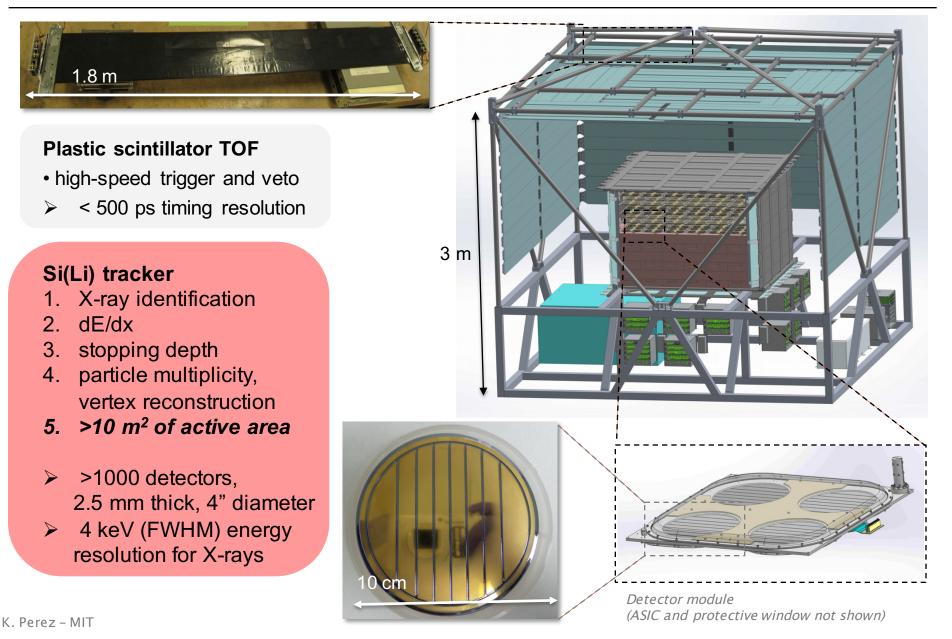


Requires technique with low-energy (E<0.25 GeV/n) range, large geometric acceptance, high background rejection

> Illustration credit: A. Lowell (UCSD)

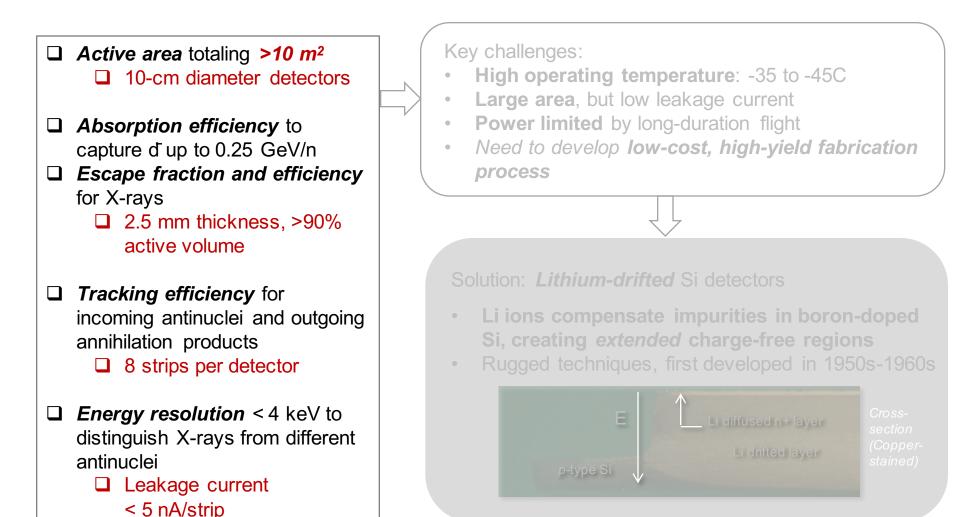
Si(Li) detectors are key to GAPS science goals





Si(Li) design principles

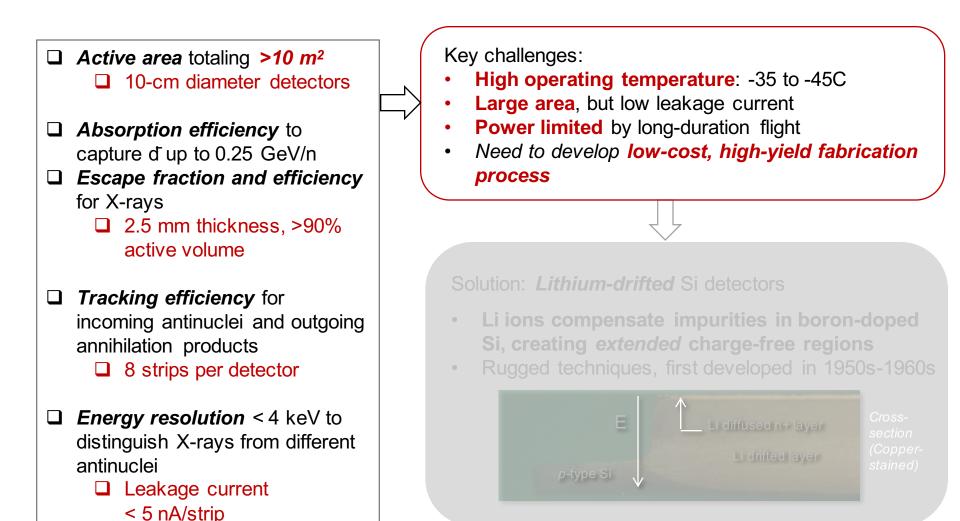




 Typical Si detectors: reverse bias produces thin intrinsic region at interface of p-type and n-type doped regions

Si(Li) design principles

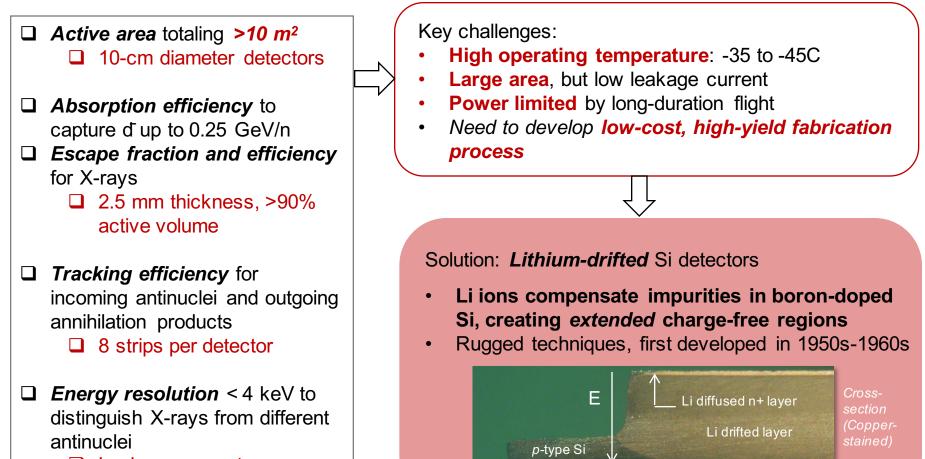




 Typical Si detectors: reverse bias produces thin intrinsic region at interface of p-type and n-type doped regions

Si(Li) design principles





Leakage current < 5 nA/strip</p>

Typical Si detectors: reverse bias produces *thin* intrinsic region at interface of p-type and n-type doped regions

GAPS Si(Li) Development Team







Excellence in Science



HEISING-SIMONS FOUNDATION





Massachusetts



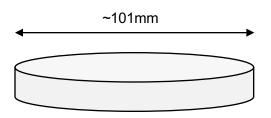








1. High-quality floating-zone (B doped) *p*-type substrate *developed by SUMCO Corp. specifically for GAPS*



Crystal orientation	$(1-1-1) \pm 1^{\circ}$
Bulk ingot lifetime	$> 400 \mu s$
Resistivity	800-2000 Ω-cm
O impurity	$< 2 \times 10^{16}$ atoms cm ⁻³
C impurity	$< 2 \times 10^{16}$ atoms cm ⁻³





1. High-quality floating-zone (B doped) *p*-type substrate *developed by SUMCO Corp. specifically for GAPS*

2. Evaporate and diffuse *n*+Li layer



Key aspects of Li:

- 1. Li is easily ionized in Si, donates electrons
 - \rightarrow n-type layer
- 2. High mobility in Si
 - ightarrow mobile positive Li ion



Example: prototype fabrication facility



1. High-quality floating-zone (B doped) *p*-type substrate *developed by SUMCO Corp. specifically for GAPS*

2. Evaporate and diffuse *n*+Li layer



3. Top-hat structure to control Li drift (UIG), evaporate Au/Ni electrodes







Example: prototype fabrication facility

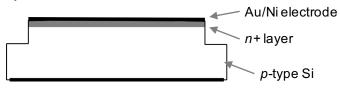


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2. Evaporate and diffuse *n*+Li layer

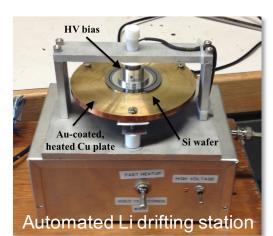


3. Top-hat structure to control Li drift (UIG), evaporate Au/Ni electrodes

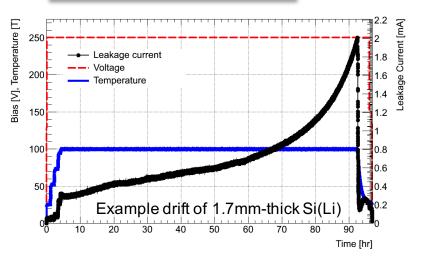




Mobile positive Li ions compensate impurities in boron-doped Si, creating *extended* charge-free regions



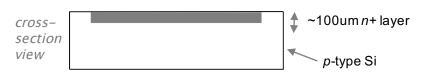
- high temperature:
 ~110 C
- constant voltage: ~500 V
- long time:
 ~90 hrs for 2.5mm



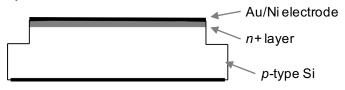


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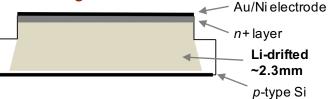
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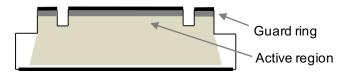
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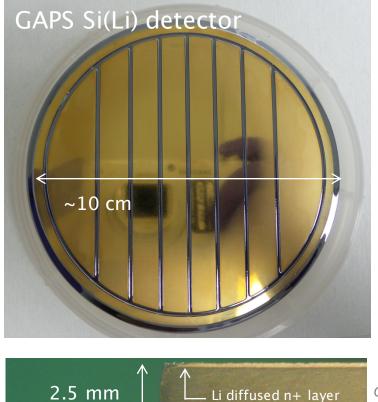


4. Drift Li through wafer



5. Cut guard ring grooves, strips (UIG).





p-type Si

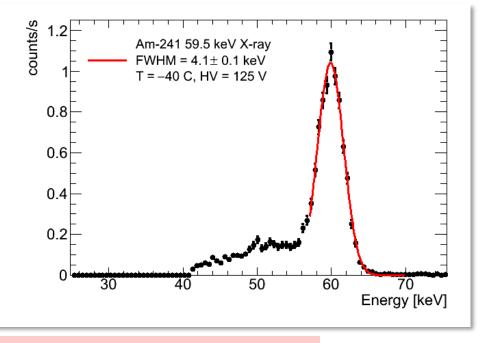
Crosssection (Copperstained)

Li drifted layer

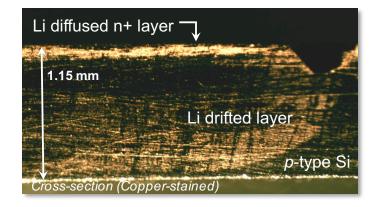
Validated low-cost technique with prototype Si(Li)

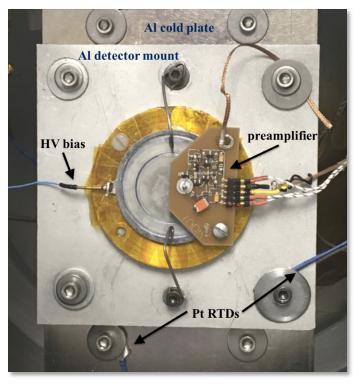


- Prototype Si(Li) detectors:
 5-cm diameter, 1-1.75 mm thick
- Low-cost fabrication scheme developed to achieve required 4 keV energy resolution at relatively high operating temperature of -40 C
- ✓ Total cost ~few hundred dollars in materials



Perez et al. NIM A905 12-21 (2018)

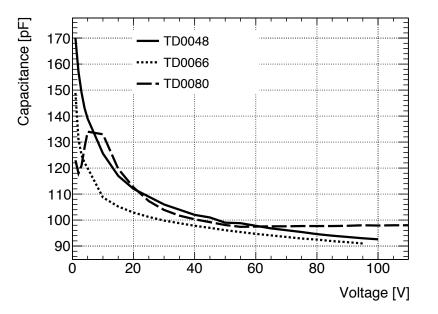




Prototype Si(Li): key diagnostics

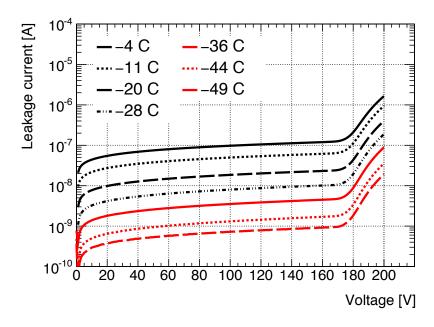


• Capacitance scales with intrinsic region width, and is used to determine the proper operating bias



 ✓ Well-functioning detector (TD0048) is >90% depleted by ~1000 V/cm (150V bias for these 1.5 mm detectors)

- Leakage current is main contributor to energy resolution
- For bulk-current dominated, decreases with temperature as I ~ exp{-E_g/2kT}



- ✓ Achieve < 0.5 nA/cm², necessary for required energy resolution performance
- Scales with temperature as expected





Partnered with **Shimadzu Corp**., a commercial producer of Si(Li) detectors with over 40 years of experience



Conventional Si(Li) for X-ray spectrometry:

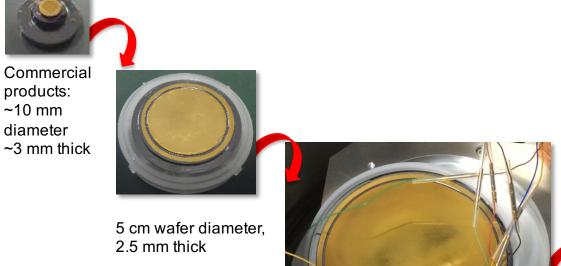
- Small diameter< 1 cm
- Low operation temperature (Liquid nitrogen temperature)

Commercial products: ~10 mm diameter ~3 mm thick

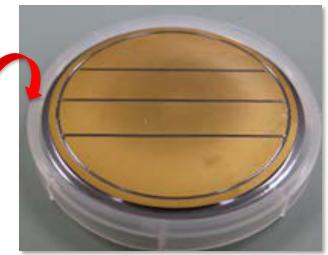




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Feasible flight design! Both 4-strip and 8-strip validated (8-strip default)





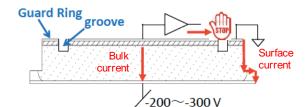
10 cm wafer diameter, 2.5 mm thick

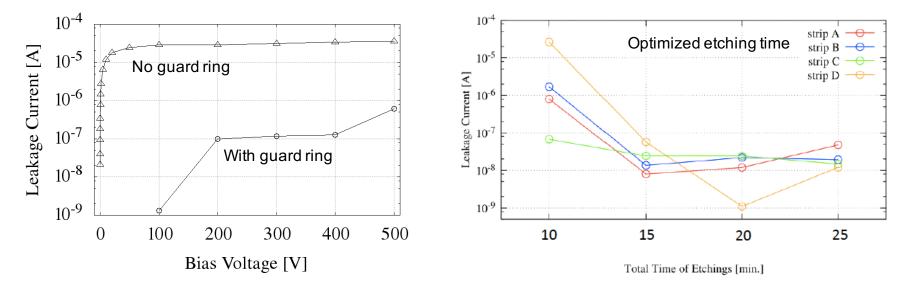
Suppressing leakage current: (1) Guard ring geometry and surface preparation



Guard ring structure prevents surface leakage current from entering readout

circuit e.g. Goulding NIM 12 249-262 (1962)





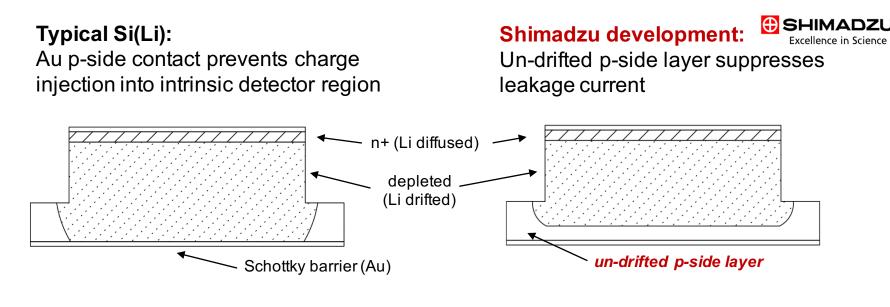
"It would be no exaggeration to say that the least understood and most time-consuming aspect of semiconductor devices is the behavior of the region where a junction intersects the surface of the crystal." – F.S. Goulding (1963)

Chemical etching of grooves:

- Removes surface impurities
- Smooths surface
- Sets proper surface state (lightly n-type)
- → Proper groove surface treatment ensures electrical isolation of detector regions, in particular the guard ring

Suppressing leakage current: (2) Optimized drifting process

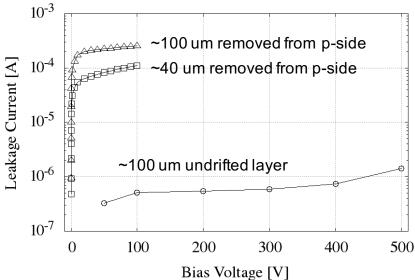




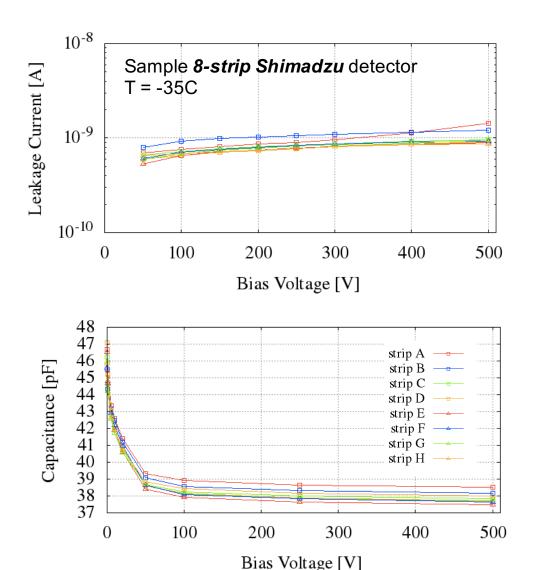
Un-drifted p-side layer suppresses leakage current

- GAPS Si(Li) only for X-rays >20 keV
- No need for thin p-side "window" in conventional Si(Li)

→ Un-drifted layer does not affect anti-nuclei identification







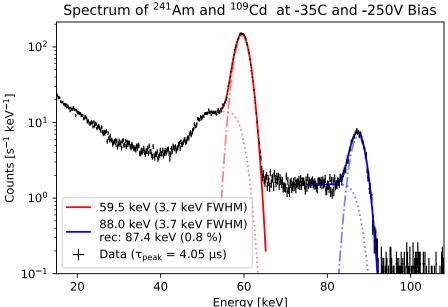
- ✓ Uniform characteristics across all strips
- ✓ Leakage is far below the 0.5 nA/cm² requirement to provide <4 keV (FWHM) energy resolution

- ✓ Capacitance indicates detector is fully depleted by our operating bias of 250 V
- ✓ Depletion corresponds to ~95% of detector thickness

M. Kozai et al. Proc. IEEE (2018)







- Energy resolution is measured at MIT using a custom low-noise, discrete-component preamplifier and flowing liquid N2 cooling system
- Same preamplifier design will be used for flight detector calibration

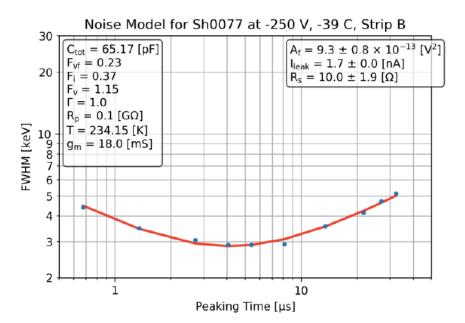
✓ Demonstrate <4 keV FWHM energy resolution and <1% energy linearity using ²⁴¹Am 59.5 keV and ¹⁰⁹Cd 88 keV X-rays Noise model combines detector characteristics with pulse shaping and readout characteristics to describe final energy resolution performance

$$ENC^2 = (2qI_{leak} + \frac{4kT}{R_p})F_i\tau$$
 Series noise
 $+4kT(R_s + \frac{1}{g_m})F_{\nu}\frac{C_{total}^2}{\tau}$ Parallel
 noise
 $+A_fC_{total}^2F_{\nu f}$ White noise

$$FWHM = 2.35\epsilon \frac{ENC}{q}$$

 ✓ Our measured energy resolution (FWHM) as a function of pulse peaking time is welldescribed by this model

Energy resolution (FWHM) as a function of peaking time for Strip B of the 8-strip Shimadzu detector Sh0077, measured at -39C and 250V operating bias using the 59.5 keV line of an Am-241 source. The red solid line shows the predicted energy resolution using the noise model with the parameters shown in the insets.







 $C_{tot} = 82.6 [pF]$

 $R_{s} = 9.9 [\Omega]$

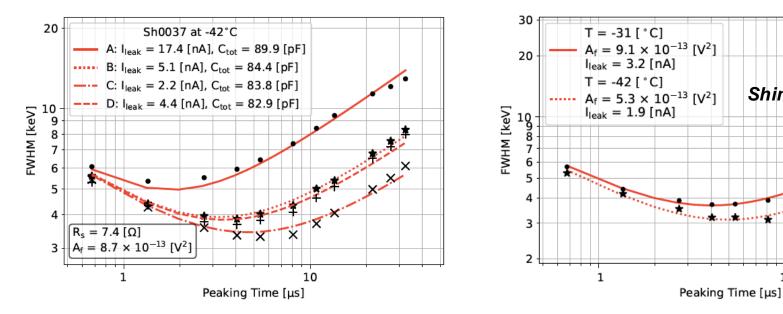
Sample **4-strip**

Shimadzu detector

10

- Energy resolution scales with leakage current as expected from the noise model
- If a detector has one strip with poor leakage current, all other strips will still be useful for X-ray detection

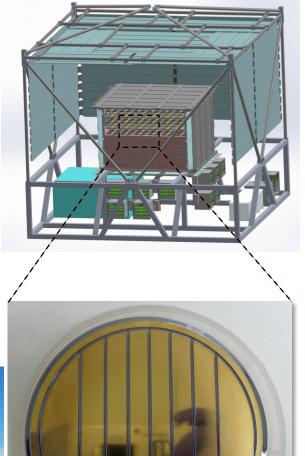
- Energy resolution and leakage current scale with temperature as expected
- We will be able to predict energy resolution as a function of in-flight temperature



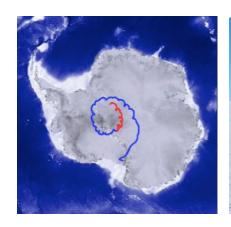
Production ongoing of >1000 Si(Li) detectors



- Large-area Si(Li) detectors have been developed to meet the unique temperature, power, cost constraints of the GAPS Antarctic balloon experiment
- Demonstrated <4 keV X-ray energy resolution at relatively high temperature of -35 to -45 C
- Evaluating production yield (estimate ~90% based on recent 10 detectors)
- Ongoing production by Shimadzu Corp. of 1100 10-cm diameter, 8-strip Si(Li) detectors, from late 2018 through early 2020



10 cm



First GAPS flight late 2020

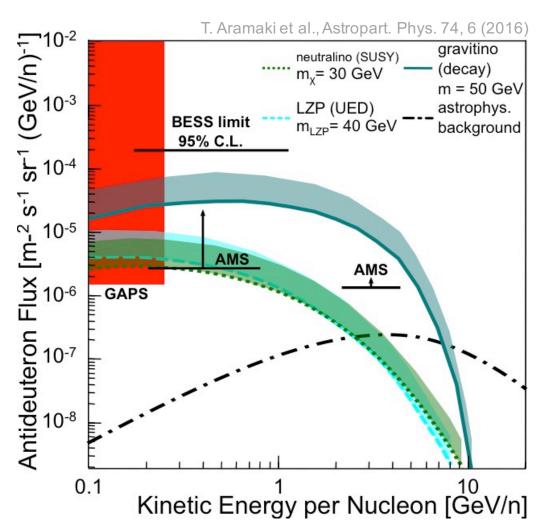
World-leading limit or detection of rare cosmic antideuterons + precision antiproton spectrum at E < 0.25 GeV/n

Backup





A generic *new physics* signature with *essentially zero* conventional astrophysical background



- Probes a variety of dark matter models that evade or complement collider, direct, or other cosmicray searches
- GAPS first experiment optimized specifically for low-energy antinuclei signatures
- First Antarctic flight: late 2020

Review of experiment and theory: Phys. Rept. 618 (2016) 1-37